

GSDBAS16JZF

Switching Diode

Product Description

The switching diode with 100V 215mA.

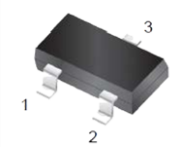
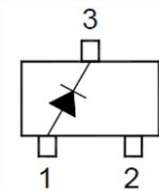
Features

- High switching speed $t_{rr} \leq 4 \text{ ns}$
- Repetitive peak reverse voltage: $V_{RRM} \leq 100 \text{ V}$

Mechanical Data

- SOT-23. Package
- RoHS Compliant and Halogen Free

Package and Pin Assignment

SOT-23		Equivalent Circuit	
			
* Pin 2 is Not Connected.			
Pin	Description	Pin	Description
1	Anode	3	Cathode

Ordering and Marking Information

GS P/N	Package	Marking	Quantity / Reel
GSDBAS16JZF	SOT-23	5D	3,000PCS
GSDBAS16JZF			
- Product Code: GSDBAS16	- Package Code: JZ for SOD-323	- Green Level: F for RoHS Compliant and Halogen Free	
Marking Information			
<div>5D</div>	- Product Code: 5D		

Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Symbol	Parameter		Value	Unit
V _{RRM}	Repetitive Peak Reverse Voltage		100	V
V _R	Reverse Voltage		80	V
I _{F(AV)}	Continuous Forward Current		215	mA
I _{FSM}	Non-Repetitive Peak Forward Surge Current	t=1μs	4	A
		t=1ms	1	
		t=1s	0.5	
I _{FRM}	Repetitive Peak Forward Current		0.5	A
P _D	Power Dissipation		350	mW
R _{θJA}	Thermal Resistance from Junction to Ambient ¹		357	°C/W
T _J	Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to +150	°C

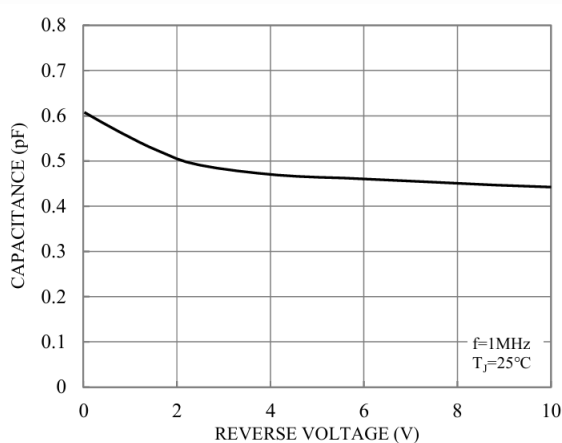
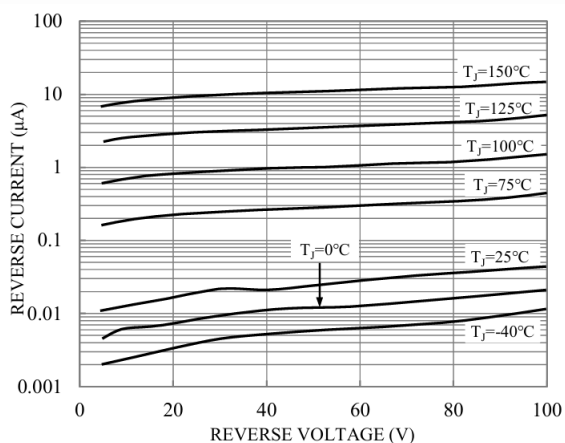
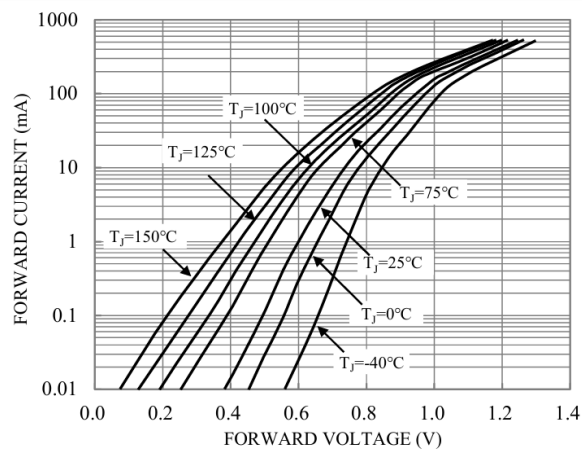
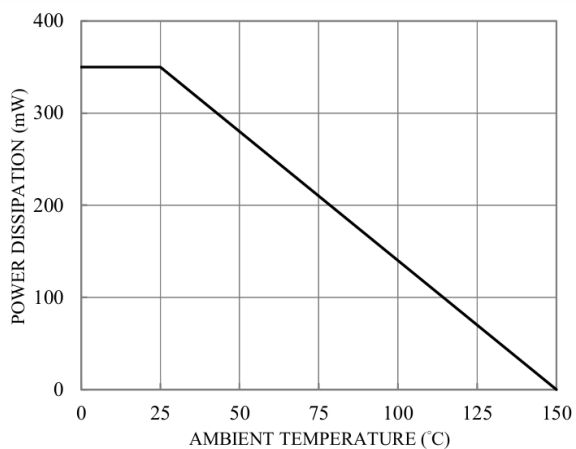
NOTE:

Device mounted on FR-4 PCB with minimum recommended pad layout.

Electrical Characteristics (T_A=25°C unless otherwise specified)

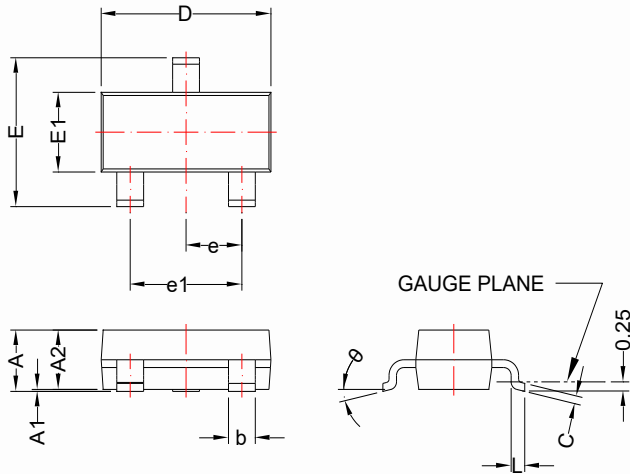
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _F	Forward Voltage	I _F =1mA			0.715	V
		I _F =10mA			0.855	
		I _F =50mA			1.000	
		I _F =150mA			1.250	
I _R	Reverse Current	V _R =25V			0.03	μA
		V _R =80V			0.5	
		V _R =25V, T _J =150°C			30	
		V _R =80V, T _J =150°C			50	
C _d	Diode Capacitance	V _R =0V, f=1MHz			2	pF
t _{rr}	Reverse Recovery Time	I _F =10mA, V _R =6V, R _L =100Ω			4	ns

Typical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise specified)

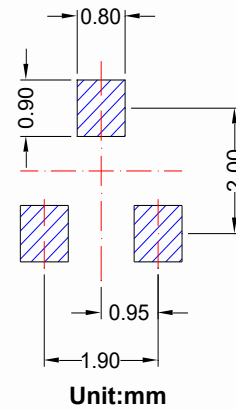


SOT-23

Package Dimension



Recommended Land Pattern



Dimensions

SYMBOL	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	0.75	1.20	0.030	0.047
A1	0.00	0.15	0.000	0.006
A2	0.70	1.10	0.028	0.043
b	0.30	0.60	0.012	0.024
c	0.08	0.20	0.003	0.008
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E1	1.20	1.40	0.047	0.055
e	0.95 BSC		0.037 BSC	
e1	1.90 BSC		0.075 BSC	
L	0.2	0.6	0.008	0.024
θ	0°	8°	0°	8°





NOTE:



Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.

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